

ATTY DOCKET NO.  
243339US3

SHEET 1 OF 1

SERIAL NO.  
10/673,173

## LIST OF REFERENCES CITED BY APPLICANT

APPLICANT  
Yukihiko NAKATA, et al.FILING DATE  
September 30, 2003GROUP  
1753

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
	AO					
	AP					
	AQ					
	AR					
	AS					
	AT					
	AU					

## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

RRB	AV	Y. NAKATA, et al., Proceedings of Int. Conf. on Rapid Thermal Processing for Future Semiconductor Device, 2 pages, "RAPID LOW TEMPERATURE PHOTO OXIDATION PROCESSING FOR ADVANCED POLY-SI TFTS", 2001
RRB	AW	Y. NAKATA, et al., Extended Abstracts of International Workshop on Gate Insulator, pages 120-123, "PHOTO OXIDATION AND PECVD STACKED GATE INSULATOR FOR POLY-SI TFTS AT 200-300 °C", November 1-2, 2001
RRB	AX	Y. NAKATA, et al., Asia Display/IDW '01, pages 375-378, "LOW TEMPERATURE GATE INSULATOR FOR POLY-SI TFTS BY COMBINATION OF PHOTO OXIDATION AND PECVD", October 16-19, 2001
	AY	<del>Y. NAKATA, et al., Spring 48<sup>th</sup> Applied Physics Related Joint Lecture Meeting, page 89, "LOW TEMPERATURE OXIDE FORMATION FOR POLY-SI TFT BY PLASMA AND LIGHT PROCESS", 2001</del>
RRB	AZ	Y. NAKATA, et al., IEICE Transactions on Electronics, vol. E85-C, no. 11, pages 1849-1853, "LOW-TEMPERATURE GATE INSULATOR FOR POLY-SI THIN FILM TRANSISTORS BY COMBINATION OF PHOTO-OXIDATION AND PLASMA ENHANCED CHEMICAL VAPOR DEPOSITION USING TETRAETHYLOXOSILICATE AND O <sub>2</sub> GASES", November 2002

☐ Additional References sheet(s) attached

Examiner

R Buhl

Date Considered 8-2005

\*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.